Dual buffer/line driver; 3-state

Rev. 3 — 6 May 2013

Product data sheet

1. General description

The 74AHC2G125 and 74AHCT2G125 are high-speed Si-gate CMOS devices. They provide a dual non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input (nOE). A HIGH at nOE causes the output to assume a high-impedance OFF-state.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

The AHCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

2. Features and benefits

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
 - ◆ HBM JESD22-A114E: exceeds 2000 V
 - MM JESD22-A115-A: exceeds 200 V
 - CDM JESD22-C101C: exceeds 1000 V
- Specified from –40 °C to +125 °C

3. Ordering information

Table 1.Ordering information

Type number	Package									
	Temperature range	Name	Description	Version						
74AHC2G125DP	–40 °C to +125 °C	TSSOP8								
74AHCT2G125DP			body width 3 mm; lead length 0.5 mm							
74AHC2G125DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package;	SOT765-1						
74AHCT2G125DC			8 leads; body width 2.3 mm							
74AHC2G125GD	–40 °C to +125 °C	XSON8								
74AHCT2G125GD			leads; 8 terminals; body $3 \times 2 \times 0.5$ mm							

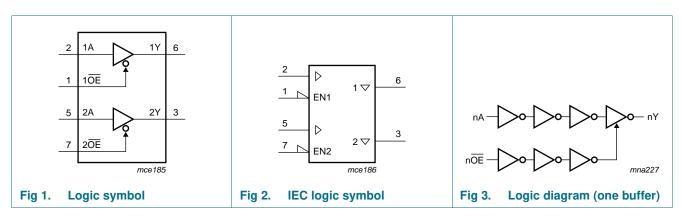


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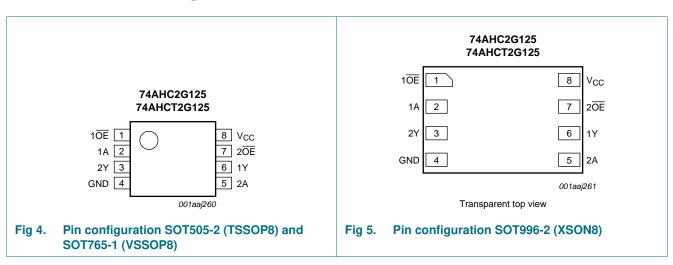
4. Marking

Table 2. Marking codes	
Type number	Marking
74AHC2G125DP	A25
74AHCT2G125DP	C25
74AHC2G125DC	A25
74AHCT2G125DC	C25
74AHC2G125GD	A25
74AHCT2G125GD	C25

5. Functional diagram



6. Pinning information



6.1 Pinning

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6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
10E, 20E	1,7	output enable input (active LOW)
1A, 2A	2, 5	data input
GND	4	ground (0 V)
1Y, 2Y	6, 3	data output
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table ^[1]		
Control	Input	Output
nOE	nA	nY
L	L	L
L	Н	Н
Н	Х	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
VI	input voltage		-0.5	+7.0	V
I _{IK}	input clamping current	V ₁ < -0.5 V	<u>[1]</u> –20	-	mA
I _{OK}	output clamping current	$V_O < -0.5 \ V$ or $V_O > V_{CC}$ + 0.5 V	<u>[1]</u> -	±20	mA
lo	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I _{CC}	supply current		-	75	mA
I _{GND}	ground current		-75	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +125 \ ^{\circ}C$	[2] _	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K. For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K. For XSON8 package: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

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9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74AHC2G125			74/	Unit		
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	0	-	5.5	V
Vo	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise	V_{CC} = 3.3 V \pm 0.3 V	-	-	100	-	-	-	ns/V
	and fall rate	$V_{CC}=5.0~V\pm0.5~V$	-	-	20	-	-	20	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C	to +85 °C	–40 °C	to +125 °C	Unit
			Min	Тур	Мах	Min	Max	Min	Max	
74AHC2	G125				•					
V _{IH}	HIGH-level	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
	input voltage	V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V _{IL}	LOW-level	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
	input voltage	$V_{CC} = 3.0 V$	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V _{OH}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_O = -50 \ \mu\text{A}; \ V_{CC} = 2.0 \ \text{V}$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -50 \ \mu\text{A}; \ V_{CC} = 3.0 \ V$	2.9	3.0	-	2.9	-	2.9	-	V
		$I_O = -50 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		$I_{O} = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_{O} = 50 \ \mu A; \ V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 50 \ \mu A; \ V_{CC} = 3.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 50 \ \mu A; V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
		$I_{O} = 8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
I _{OZ}	OFF-state output current	$V_{I} = V_{CC} \text{ or GND};$ $V_{CC} = 5.5 \text{ V}$	-	-	0.25	-	2.5	-	10	μA
lı	input leakage current		-	-	0.1	-	1.0	-	2.0	μA
I _{CC}	supply current		-	-	1.0	-	10	-	40	μA

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Voltages	are referenced	to GND (ground = 0 V).								
Symbol	Parameter	Conditions		25 °C		–40 °C	to +85 °C	–40 °C	to +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
CI	input capacitance		-	1.5	10	-	10	-	10	pF
74AHCT	2G125									
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = -50 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -8.0 mA	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	V _{OL} LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
I _{OZ}	OFF-state output current	$V_1 = V_{CC}$ or GND; $V_{CC} = 5.5 V$	-	-	0.25	-	2.5	-	10	μA
lı	input leakage current	$\label{eq:VI} \begin{array}{l} V_{I} = 5.5 \text{ V or GND}; \\ V_{CC} = 0 \text{ V to } 5.5 \text{ V} \end{array}$	-	-	0.1	-	1.0	-	2.0	μA
I _{CC}	supply current		-	-	1.0	-	10	-	40	μA
ΔI_{CC}	additional supply current	per input pin; $V_I = 3.4 V$; other inputs at V_{CC} or GND; $I_O = 0 A$; $V_{CC} = 5.5 V$	-	-	1.35	-	1.5	-	1.5	mA
CI	input capacitance		-	1.5	10	-	10	-	10	pF

Table 7. Static characteristics ... continued Voltages are referenced to GND (ground = 0.)

11. Dynamic characteristics

Table 8.Dynamic characteristics

GND = 0 V; for test circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
				Min	Тур	Max	Min	Max	Min	Max	
74AHC2	G125										
t _{pd} propag delay	propagation	nA to nY; see Figure 6	[1]								
	delay	$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	[2]								
		C _L = 15 pF		-	4.7	8.0	1.0	9.5	1.0	11.5	ns
		C _L = 50 pF		-	6.6	11.5	1.0	13.0	1.0	14.5	ns
		V_{CC} = 4.5 V to 5.5 V	[3]								
		C _L = 15 pF		-	3.4	5.5	1.0	6.5	1.0	7.0	ns
		C _L = 50 pF		-	4.8	7.5	1.0	8.5	1.0	9.5	ns

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Symbol	Parameter	Conditions			25 °C		–40 °C 1	to +85 °C	–40 °C to +125 °C		Uni
				Min	Тур	Max	Min	Max	Min	Max	
en	enable time	nOE to nY; see Figure 7	[1]								
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	[2]								
		C _L = 15 pF		-	5.0	8.0	1.0	9.5	1.0	11.5	ns
		C _L = 50 pF		-	6.9	11.5	1.0	13.0	1.0	14.5	ns
		$V_{CC} = 4.5 \text{ V} \text{ to } 5.5 \text{ V}$	[3]								
		C _L = 15 pF		-	3.6	5.1	1.0	6.0	1.0	6.5	ns
		C _L = 50 pF		-	4.9	7.5	1.0	8.5	1.0	9.5	ns
dis	disable time	nOE to nY; see Figure 7	[1]								
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	[2]								
		C _L = 15 pF		-	6.0	9.7	1.0	11.5	1.0	12.5	ns
		C _L = 50 pF		-	8.3	13.2	1.0	15.0	1.0	16.5	ns
		$V_{CC} = 4.5 \text{ V} \text{ to } 5.5 \text{ V}$	[3]								
		C _L = 15 pF		-	4.1	6.8	1.0	8.0	1.0	8.5	ns
		C _L = 50 pF		-	5.7	8.8	1.0	10.0	1.0	11.0	ns
C _{PD}	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF}; f_i = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	<u>[4]</u>	-	9	-	-	-	-	-	рF
74AHCT	2G125										
pd	propagation	nA to nY; see Figure 6	[1]								
	delay	$V_{CC} = 4.5 \text{ V}$ to 5.5 V	[3]								
		C _L = 15 pF		-	3.4	5.5	1.0	6.5	1.0	6.5	ns
		C _L = 50 pF		-	4.8	7.5	1.0	8.5	1.0	8.5	ns
en	enable time	nOE to nY; see Figure 7	[1]								
		$V_{CC} = 4.5 \text{ V}$ to 5.5 V	[3]								
		C _L = 15 pF		-	3.9	5.1	1.0	6.0	1.0	6.0	ns
		C _L = 50 pF		-	5.1	7.5	1.0	8.5	1.0	8.5	ns
dis	disable time	nOE to nY; see Figure 7	[1]								
		V_{CC} = 4.5 V to 5.5 V	[3]								
		C _L = 15 pF		-	4.5	6.8	1.0	8.0	1.0	8.0	ns
		C _L = 50 pF		-	6.1	8.8	1.0	10.0	1.0	10.0	ns

Table 8.Dynamic characteristics ... continuedGND = 0 V: for test circuit see Figure 8.

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Symbol	nbol Parameter Conditions			25 °C –		–40 °C to +85 °C		–40 °C to +125 °C		Uni	
				Min	Тур	Max	Min	Max	Min	Max	
C _{PD}	•	per buffer; $C_L = 50 \text{ pF}; f_i = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	[4]	-	11	-	-	-	-	-	pF

Table 8. Dynamic characteristics ... continued

[1] t_{pd} is the same as t_{PLH} and t_{PHL} . t_{en} is the same as t_{PZL} and t_{PZH} .

 t_{dis} is the same as t_{PLZ} and t_{PHZ} .

[2] Typical values are measured at V_{CC} = 3.3 V.

- [3] Typical values are measured at $V_{CC} = 5.0$ V.
- [4] C_{PD} is used to determine the dynamic power dissipation P_D (μ W).

 P_{D} = $C_{PD} \times V_{CC}{}^{2} \times f_{i}$ + Σ ($C_{L} \times V_{CC}{}^{2} \times f_{o}$) where:

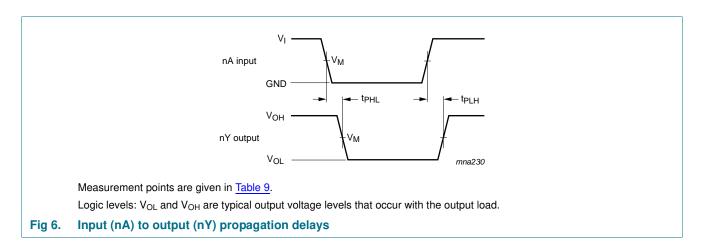
 $f_i = input frequency in MHz;$

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts.

12. Waveforms



Dual buffer/line driver; 3-state

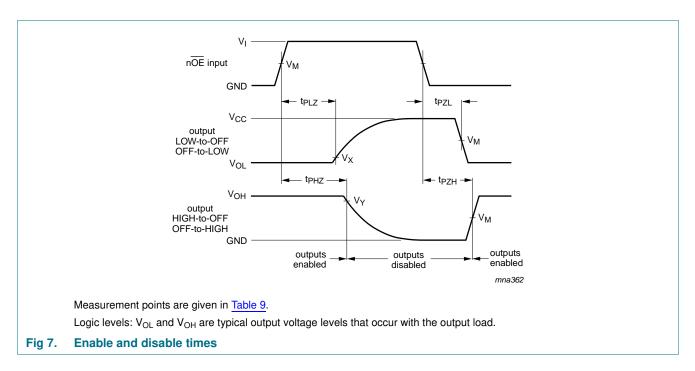


Table 9.Measurement points

Туре	Input	Output					
	V _M	V _M	V _X	V _Y			
74AHC2G125	0.5V _{CC}	0.5V _{CC}	V_{OL} + 0.3 V	$V_{OH} - 0.3 V$			
74AHCT2G125	1.5 V	0.5V _{CC}	$V_{OL} + 0.3 V$	$V_{OH} - 0.3 V$			

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74AHC2G125; 74AHCT2G125

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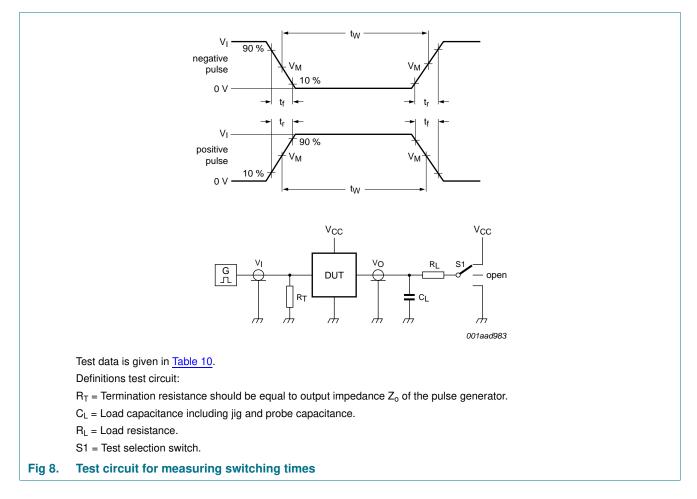


Table 10. Test data

Туре	Input		Load		S1 position		
	VI	t _r , t _f	CL	RL	t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
74AHC2G125	V _{CC}	\leq 3 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}
74AHCT2G125	3 V	\leq 3 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}

Dual buffer/line driver; 3-state

13. Package outline

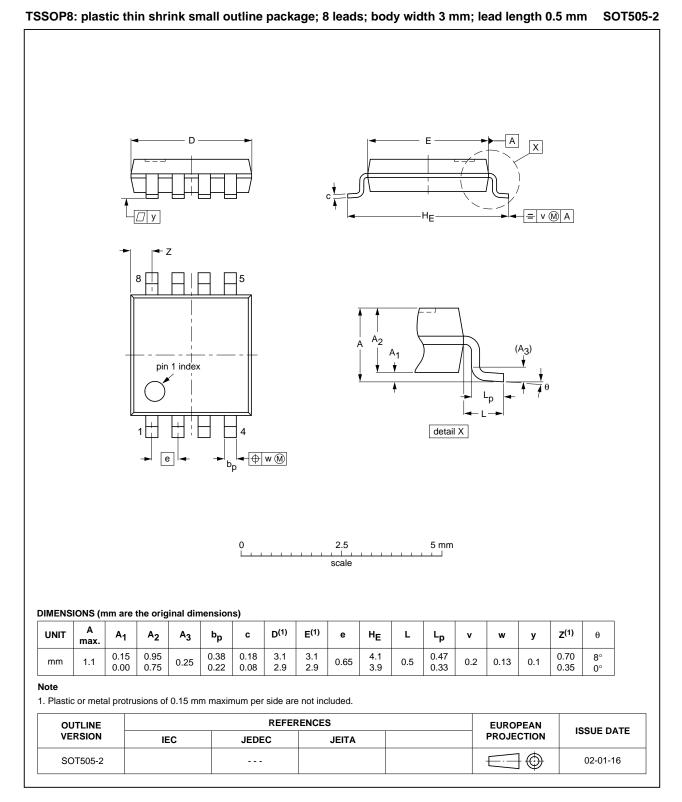


Fig 9. Package outline SOT505-2 (TSSOP8)

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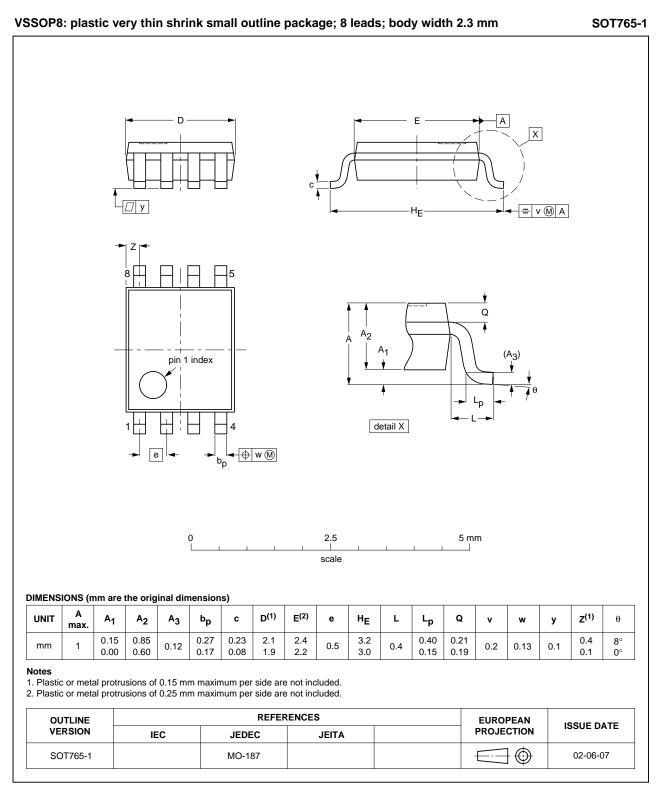
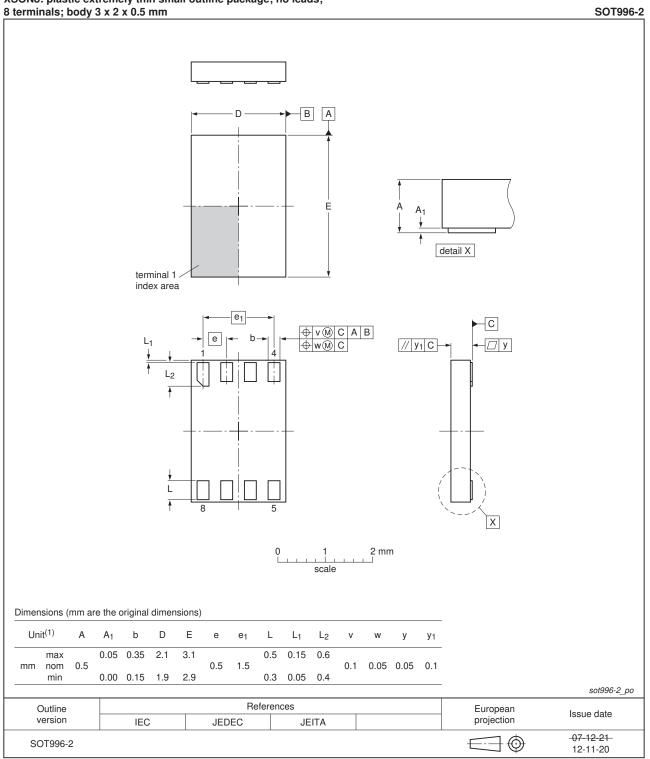


Fig 10. Package outline SOT765-1 (VSSOP8)

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XSON8: plastic extremely thin small outline package; no leads;

Fig 11. Package outline SOT996-2 (XSON8)

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14. Abbreviations

Table 11.	Abbreviations		
Acronym	Description		
CMOS	Complementary Metal Oxide Semiconductor		
CDM	Charged Device Model		
DUT	Device Under Test		
ESD	ElectroStatic Discharge		
HBM	Human Body Model		
MM	Machine Model		
TTL	Transistor-Transistor Logic		

15. Revision history

Table 12. Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT2G125 v.3	20130506	Product data sheet	-	74AHC_AHCT2G125 v.2
Modifications:	 For type nun XSON8. 	nber 74AHC2G125GD and 74/	AHCT2G125GE	OXSON8U has changed to
74AHC_AHCT2G125 v.2	20081222	Product data sheet	-	74AHC_AHCT2G125 v.1
Modifications:		f this data sheet has been red NXP Semiconductors.	esigned to com	ply with the new identity
	 Legal texts h 	ave been adapted to the new	company name	where appropriate.
	 Added type r 	number 74AHC2G125GD and	74AHCT2G125	GD (XSON8U package).
74AHC_AHCT2G125 v.1	20040113	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Dual buffer/line driver; 3-state

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